ITS41k0S-ME-N

Smart High-Side NMOS-Power Switch

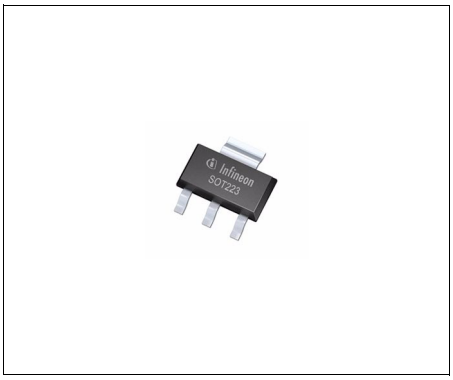
Data Sheet

Rev 1.0, 2012-09-01

Standard Power

RoHS

1 Overview



PG-SOT223-4

Features

- Current controlled input
- Capable of driving all kind of loads (inductive, capacitive and resitive)
- Negative voltage clamped at output with inductive loads
- Current limitation
- Very low standby current
- Thermal shutdown with restart
- Overload protection
- Short circuit protection
- Overvoltage protection (including load dump)
- Reverse battery protection
- Loss of GND and loss of Vbb protection
- ESD-Protection
- Improved electromagnetic compatibility (EMC)
- Green Product (RoHS compliant)

ITS41k0S-ME-N is not qualified and manufactured according to the requirements of Infineon Technologies with regards to automotive and/or transportation applications.

Description

The ITS41k0S-ME-N is a protected 1 Ω single channel Smart High-Side NMOS-Power Switch in a PG-SOT223-4 package with charge pump and current controlled input, monolithically integrated in a smart power technology.

Product Summary

Overvoltage protection $V_{SAZ\ min}$= 62V
Operating voltage range 4,9V < V_S < 60V
On-state resistance R_{DSON} typ 800 mΩ
Operating Temperature range Tj = -40°C to 125°C

Application

- All types of resistive, inductive and capacitive loads
- Current controlled power switch for 12V, 24V and 45V DC in industrial applications
- Driver for electromagnetic relays
- Signal amplifier

Type	Package	Marking
ITS41k0S-ME-N	PG-SOT223-4	I1k0SN

2 Block Diagram and Terms

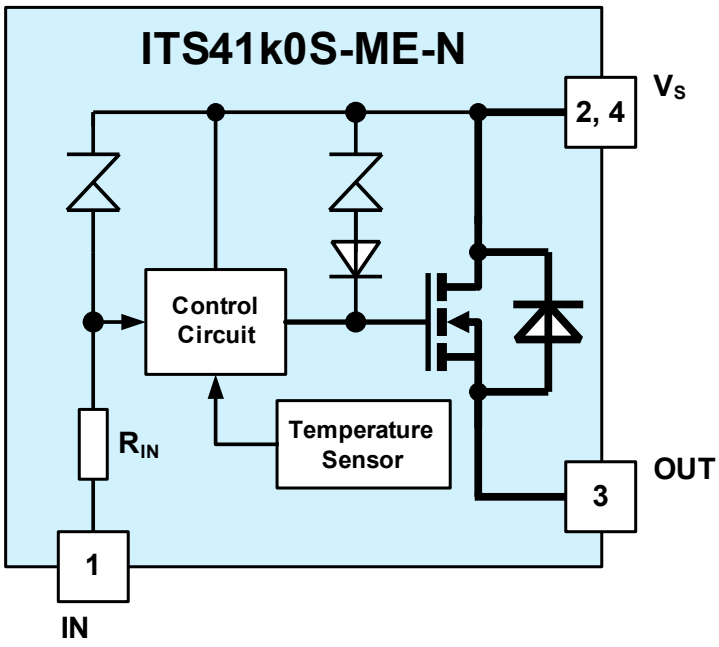


Figure 1 Block diagram

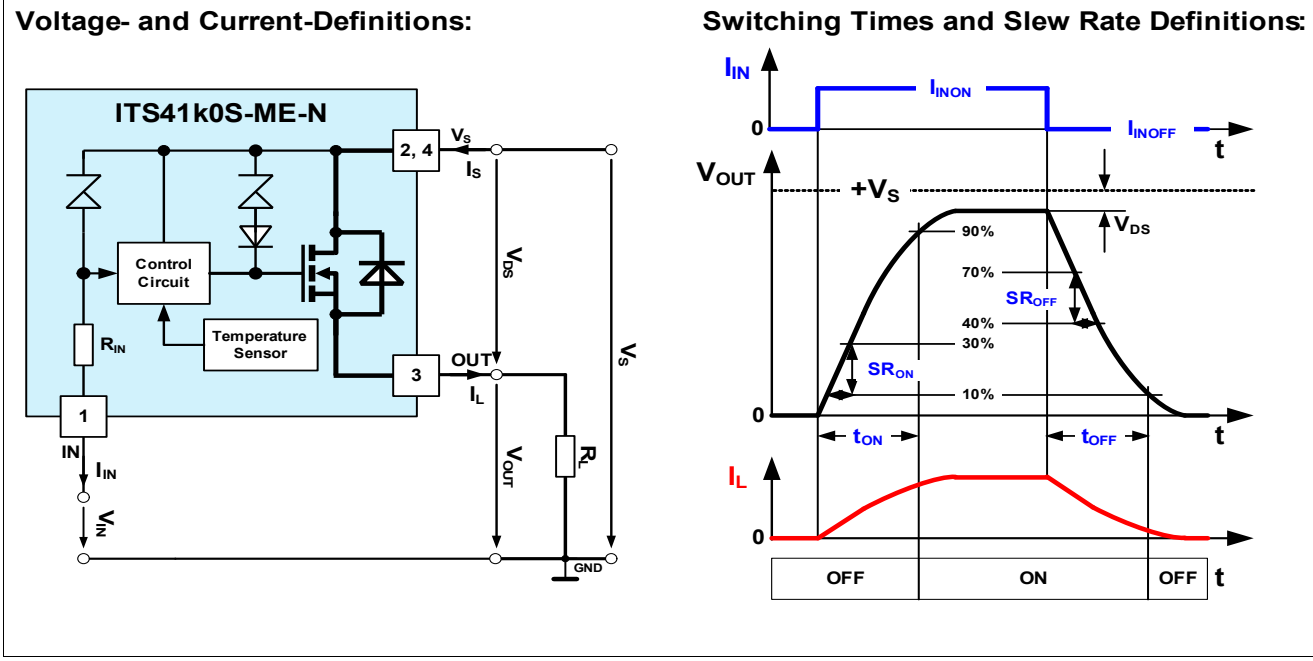


Figure 2 Terms - parameter definition

3 Pin Configuration

3.1 Pin Assignment

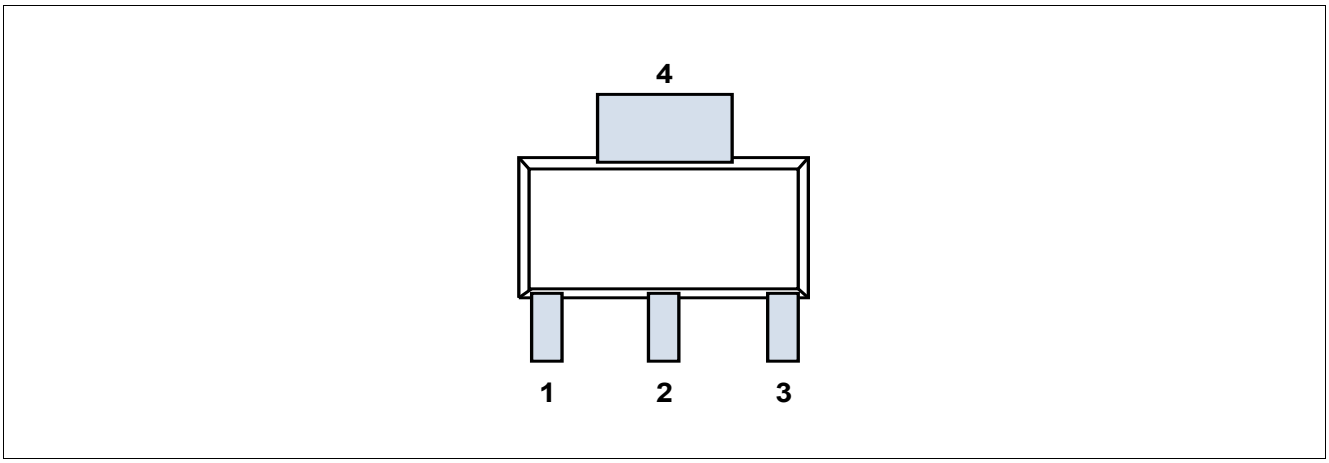


Figure 3 Pin configuration top view, PG-SOT223-4

3.2 Pin Definitions and Functions

Pin	Symbol	Function
1	IN	Input, activates the power switch in case of connection to GND
2	VS	Supply voltage
3	OUT	Output to the load
4	VS	Supply voltage

4 General Product Characteristics

4.1 Absolute Maximum Ratings

Table 1 Absolute maximum ratings [1]Tj = 25°C all voltages with respect to ground. Currents flowing into the device unless otherwise specified in chapter "Block Diagram and Terms"

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Supply voltage VS						
Voltage	V_S		60	V		4.1.1
Output stage OUT						
Output Current; (Short circuit current see electrical characteristics)	I_{OUT}	self limited			A	4.1.2
Input IN						
Input Current	I_{IN}	-15	15	mA		4.1.3
Temperatures						
Junction Temperature	T_j	-40	125	°C		4.1.4
Storage Temperature	T_{stg}	-55	125	°C		4.1.5
Power dissipation						
Ta = 25 °C[2]	P_{tot}		1.7	W		4.1.6
Inductive load switch-off energy dissipation						
Tj = 150 °C; IL=0.15A; single pulse [1]	E_{AS}		1000	mJ		4.1.7
ESD Susceptibility						
ESD susceptibility (input pin)	V_{ESD}	-1	1	kV	HBM[3]	4.1.8
ESD susceptibility (all other pins)	V_{ESD}	-5	5	kV	HBM[3]	4.1.9

1) Not subject to production test, specified by design

2) Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm2 (one layer, 70mm thick) copper area for Vbb connection. PCB is vertical without blown air

3) ESD susceptibility HBM according to EIA/JESD 22-A 114.

Note: Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" the normal operating range. Protection functions are not designed for continuous or repetitive operation.

4.2 Functional Range

Table 2 Functional Range

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
Nominal Operating Voltage	V_S	4.9	–	60	V	V_S increasing	4.2.1

Note: Within the functional range the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the related electrical characteristics table.

4.3 Thermal Resistance

This thermal data was generated in accordance with JEDEC JESD51 standards.

More information on www.jedec.org.

Table 3 Thermal Resistance[1)]

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
PG-SOT223-4							
Junction to Case, Exposed pad	R_{thjc}	–	40.5	–	K/W		4.3.1
Junction to ambient	R_{thJA_1s0p}	–	145.4	–	K/W	2)	4.3.2
Junction to ambient	$R_{thJA\_1s0p\_300mm}$	–	77.2	–	K/W	3)	4.3.3
Junction to ambient	$R_{thJA\_1s0p\_600mm}$	–	66.2	–	K/W	4)	4.3.4
Junction to ambient	R_{thJA_2s2p}	–	57.8	–	K/W	5)	4.3.5
Junction to ambient	$R_{thJA\_2s2pvia}$	–	52.9	–	K/W	6)	4.3.6

1) Not subject to production test, specified by design

2) Specified R_{thJA} value is according to Jedec JESD51-3 at natural convection on FR4 1s0p board, footprint; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 1x 70µm Cu.

3) Specified R_{thJA} value is according to Jedec JESD51-3 at natural convection on FR4 1s0p board, Cu, 300mm^2; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 1x 70µm Cu.

4) Specified R_{thJA} value is according to Jedec JESD51-3 at natural convection on FR4 1s0p board, 600mm^2; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 1x 70µm Cu.

5) Specified R_{thJA} value is according to Jedec JESD51-2,-5,-7 at natural convection on FR4 2s2p board; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 2 inner copper layers (2 x 70µm Cu, 2 x 35µm Cu).

6) Specified R_{thJA} value is according to Jedec JESD51-2,-5,-7 at natural convection on FR4 2s2p board with two thermal vias; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 2 inner copper layers (2 x 70µm Cu, 2 x 35µm Cu. The diameter of the two vias are equal 0.3mm and have a plating of 25um with a copper heatsink area of 3mm x 2mm). JEDEC51-7: The two plated-through hole vias should have a solder land of no less than 1.25 mm diameter with a drill hole of no less than 0.85 mm diameter.

5 Electrical Characteristics

Table 4 **V_S = 9V to 60V; Tj = -40°C to 125°C; all voltages with respect to ground. Currents flowing into the device unless otherwise specified in chapter "Block Diagram and Terms". Typical values at Vs = 13.5V, Tj = 25°C**

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
Powerstage							
NMOS ON Resistance	R_{DSON}	–	0.8	1.5	Ω	I_{OUT}= 150mA; T_j = 25°C; IN conected to GND	5.0.1
NMOS ON Resistance	R_{DSON}	–	1.5	3.0	Ω	I_{OUT}= 150mA; T_j = 125°C; IN conected to GND	5.0.2
NMOS ON Resistance	R_{DSON}	–	2	5	Ω	I_{OUT}= 50mA; T_j = 25°C; V_S = 6V; IN conected to GND	5.0.3
Nominal Load Current [1]; device on PCB [2]	I_{LNOM}	0.2	–	–	A	T_a = 85°C; T_j = 125°C;	5.0.4
Timings of Power Stages							
Turn ON Time [3] (to 90% of V_{out}); V_S to GND transition of V_{IN}	t_{ON}	–	–	125 [4]	µs	V_S=13.5V; R_L = 270Ω	5.0.5
Turn ON Time [3] (to 90% of V_{out}); V_S to GND transition of V_{IN}	t_{ON}	–	45	100	µs	V_S=13.5V; R_L = 270Ω; T_j = 25°C	5.0.6
Turn OFF Time [3] (to 10% of V_{out}); GND to V_S transition of V_{IN}	t_{OFF}	–	–	175 [4]	µs	V_S=13.5V; R_L = 270Ω	5.0.7
Turn OFF Time [3] (to 10% of V_{out}); GND to V_S transition of V_{IN}	t_{OFF}	–	40	140	µs	V_S=13.5V; R_L = 270Ω; T_j = 25°C	5.0.8
ON-Slew Rate [3] (10 to 30% of V_{out}); V_S to GND transition of V_{IN}	SR_{ON}	–	–	6 [4]	V / µs	V_S=13.5V; R_L = 270Ω	5.0.9
ON-Slew Rate [3] (10 to 30% of V_{out}); V_S to GND transition of V_{IN}	SR_{ON}	–	1.3	4.0	V / µs	V_S=13.5V; R_L = 270Ω; T_j = 25°C	5.0.10
OFF-Slew Rate [3] (70 to 40% of V_{out}); GND to V_S transition of V_{IN}	SR_{OFF}	–	–	8 [4]	V / µs	V_S=13.5V; R_L = 270Ω	5.0.11
OFF-Slew Rate [3] (70 to 40% of V_{out}); GND to V_S transition of V_{IN}	SR_{OFF}	–	1.7	4.0	V / µs	V_S=13.5V; R_L = 270Ω; T_j = 25°C	5.0.12
Standby current consumption							

Table 4 **V_S = 9V to 60V; Tj = -40°C to 125°C; all voltages with respect to ground. Currents flowing into the device unless otherwise specified in chapter "Block Diagram and Terms". Typical values at Vs = 13.5V, Tj = 25°C**

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
Standby current	I_{SOFF}	–	2	10	µA	IN open	5.0.13
Protection functions [5]							
Initial peak short circuit current limit IN conected to GND	I_{LSCP}	–	–	1.2	A	T_j = -40°C; V_S = 13.5V t_m = 100µs	5.0.14
Initial peak short circuit current limit IN conected to GND	I_{LSCP}	–	0.9	–	A	T_j = 25°C; V_S = 13.5V t_m = 100µs	5.0.15
Initial peak short circuit current limit IN conected to GND	I_{LSCP}	0.2	–	–	A	T_j =125°C; V_S = 13.5V t_m = 100µs	5.0.16
Repetitive short circuit current limit IN conected to GND	I_{LSCR}	–	0.7	–	A	–	5.0.17
Output clamp at V_{OUT} = V_S - V_{DSCL} (inductive load switch off)	V_{DSCL}	60	–	–	V	I_S = 4mA	5.0.18
Overvoltage protection	V_{SAZ}	62	68	–	V	I_S = 1mA	5.0.19
Thermal overload trip temperature [4]	T_{jTrip}	150	–	–	°C	–	5.0.20
Thermal hysteresis [4]	T_{HYS}		10	–	°C	–	5.0.21
Input interface							
Off state input current	I_{INOFF}	–	–	0.05	mA	T_j = -25°C; R_L = 270Ω; V_{OUT} =< 0.1V	5.0.22
Off state input current	I_{INOFF}	–	–	0.04	mA	T_j = 125°C; R_L = 270Ω; V_{OUT} =< 0.1V	5.0.23
On state input current; IN connected to GND [6]	I_{INON}	–	0.3	1.0	mA	–	5.0.24
Input resistance	R_{IN}	0.5	1.0	2.5	kΩ	–	5.0.25
Reverse Battery							
Continuous reverse drain current	I_{DREV}	–	–	0.2	A	–	5.0.26
Forward voltage of the drain-source reverse diode	V_{FDS}	–	600	–	mV	I_{FDS} = 200mA I_{IN} =< 0.05mA	5.0.27

1) Nominal Load Current is limited by the current limitation; see protection function data

2) Device on 50mm x 50mm x 1,5mm epoxy FR4 PCB with 6cm² (one layer copper 70um thick) copper area for supply voltage connection. PCB in vertical position without blown air

3) Timing values only with high input slewrates (t_{rIN} = t_{fIN} <= 50ns); otherwise slower

4) Not tested in production

5) Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

6) Driver circuit must be able to sink currents > 1mA

6 Application Information

6.1 Application Diagram

The following information is given as a hint for the implementation of the device only and shall not be regarded as a description or warranty for a certain functionality, condition or quality of the device.

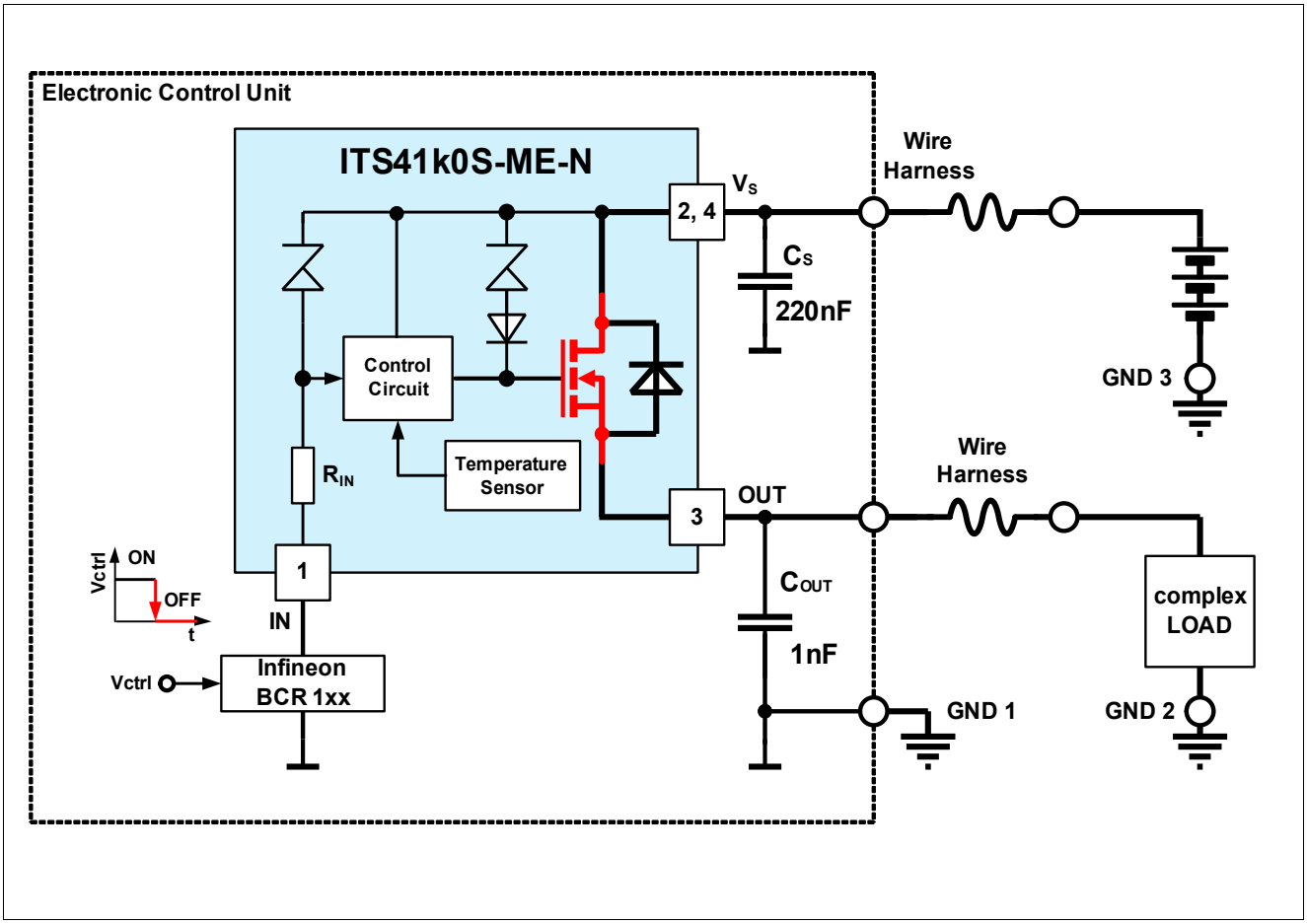


Figure 4 Application Diagram

The **ITS41k0S-ME-N** can be connected directly to a supply network. It is recommended to place a ceramic capacitor (e.g. C_S = 220nF) between supply and GND to avoid line disturbances. Wire harness inductors/resistors are sketched in the application circuit above.

The complex load (resistive, capacitive or inductive) must be connected to the output pin OUT.

A built-in current limit protects the device against destruction.

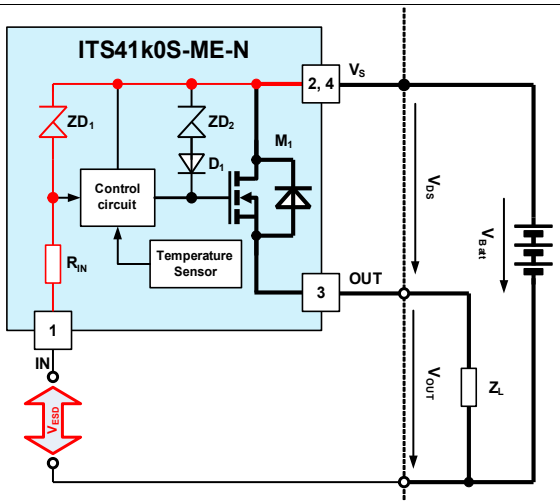
The **ITS41k0S-ME-N** can be switched on and off with a low power levelshifter switch e.g. Infineon BCR1xx.

The IN pin must be pulled down to GND potential to switch the **ITS41k0S-ME-N** on. If no current is pulled down, the IN-node will float up to V_S potential by an internal pull up. In this mode the **ITS41k0S-ME-N** is deactivated with very low current consumption.

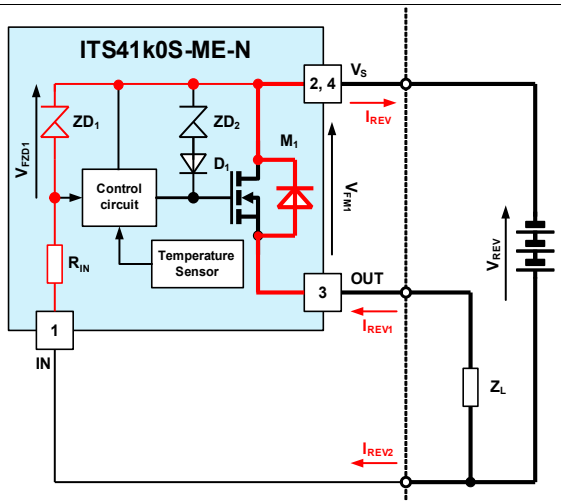
The output voltage slope is controlled during on and off transistion to minimize emissions. Only a small Cercap C_{OUT} =1nF is recommended to attenuate RF noise.

In the following chapters the main features, some typical waverforms and the protection behaviour of the **ITS41k0S-ME-N** is shown. For further details please refer to application notes on the Infineon homepage.

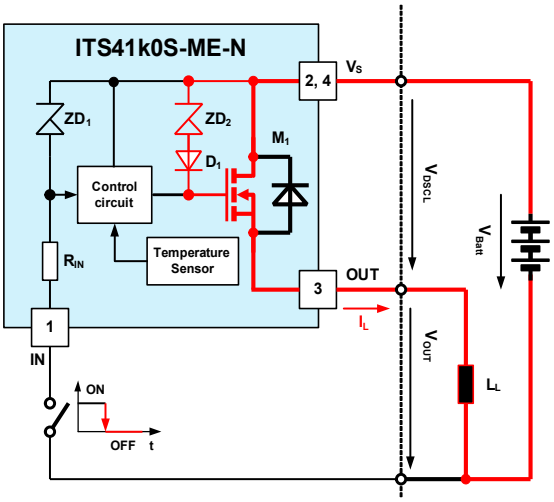
6.2 Special features



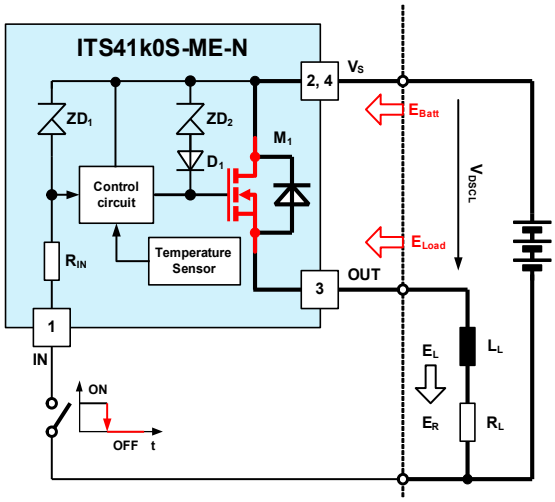
If Over-Voltage is applied to the V_S-Pin:
Voltage is limited to VZD1; Current can be calculated:
$I_{ZD1} = (V_S - V_{ZD1}) / R_{IN}$
In case of ESD Pulse on the input pin there is in both polarities a peak current $I_{INpeak} \sim V_{ESD} / R_{IN}$
The control unit is protected in both cases by the Zenerdiode ZD1



If reverse Voltage is applied to the device:
1.) Current via Load Resistance RL:
$I_{Rev1} = (V_{REV} - V_{FM1}) / R_L$
2.) Current via Input Resistance RIN:
$I_{REV2} = (V_{REV} - V_{FZD1}) / R_{IN}$
Both currents will sum up to:
$I_{REV} = I_{REV1} + I_{REV2}$



When an inductive load is switched off a current path must be established until the current is sloped down to zero (all energy removed from the inductive load).
For that purpose the series combination ZD2 and D1 is connceted between Gate and Drain of the power DMOS.
When the device is switched off, the voltage at OUT turns negative until V_{DSCL} is reached.
The Voltage on the incutive load is the difference between V_{DSCL} and V_S.



Energy stored in the load inductance is given by :
$E_L = I_L^2 * L/2$
While demagnetizing the load inductance the energy dissipated by the Power-DMOS is:

$E_{AS} = E_S + E_L - E_R$

With an approximate solution for $R_L > 0\Omega$:

$E_{AS} = (I_L * L) / (2 * R_L) * (V_S + V_{DSCL}) * \ln((1 + (I_L * R_L) / V_{DSCL})$

Figure 5 Special Feature descriptions

6.3 Typical Application Waveforms

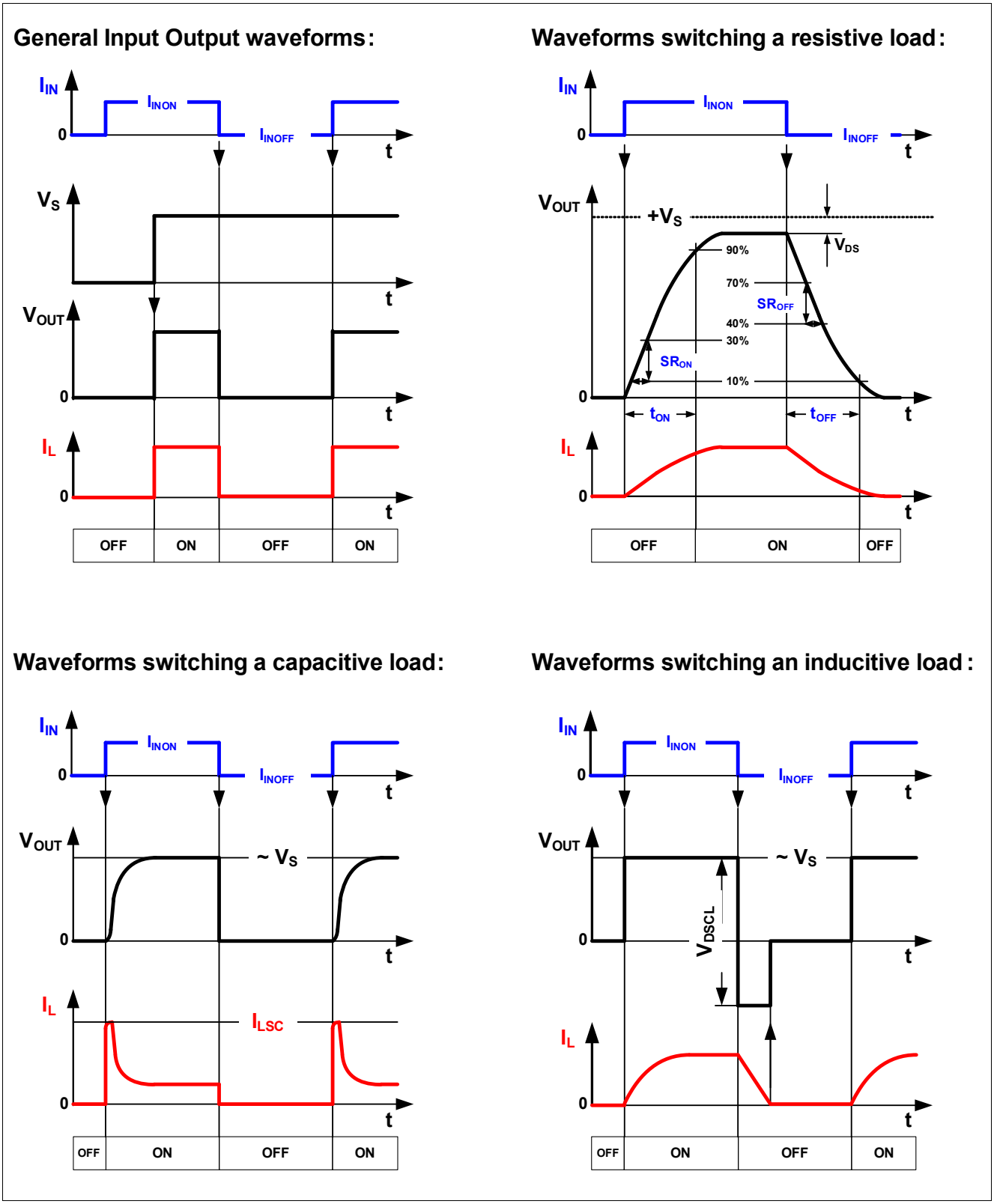


Figure 6 Typical application waveforms

6.4 Protection behavior

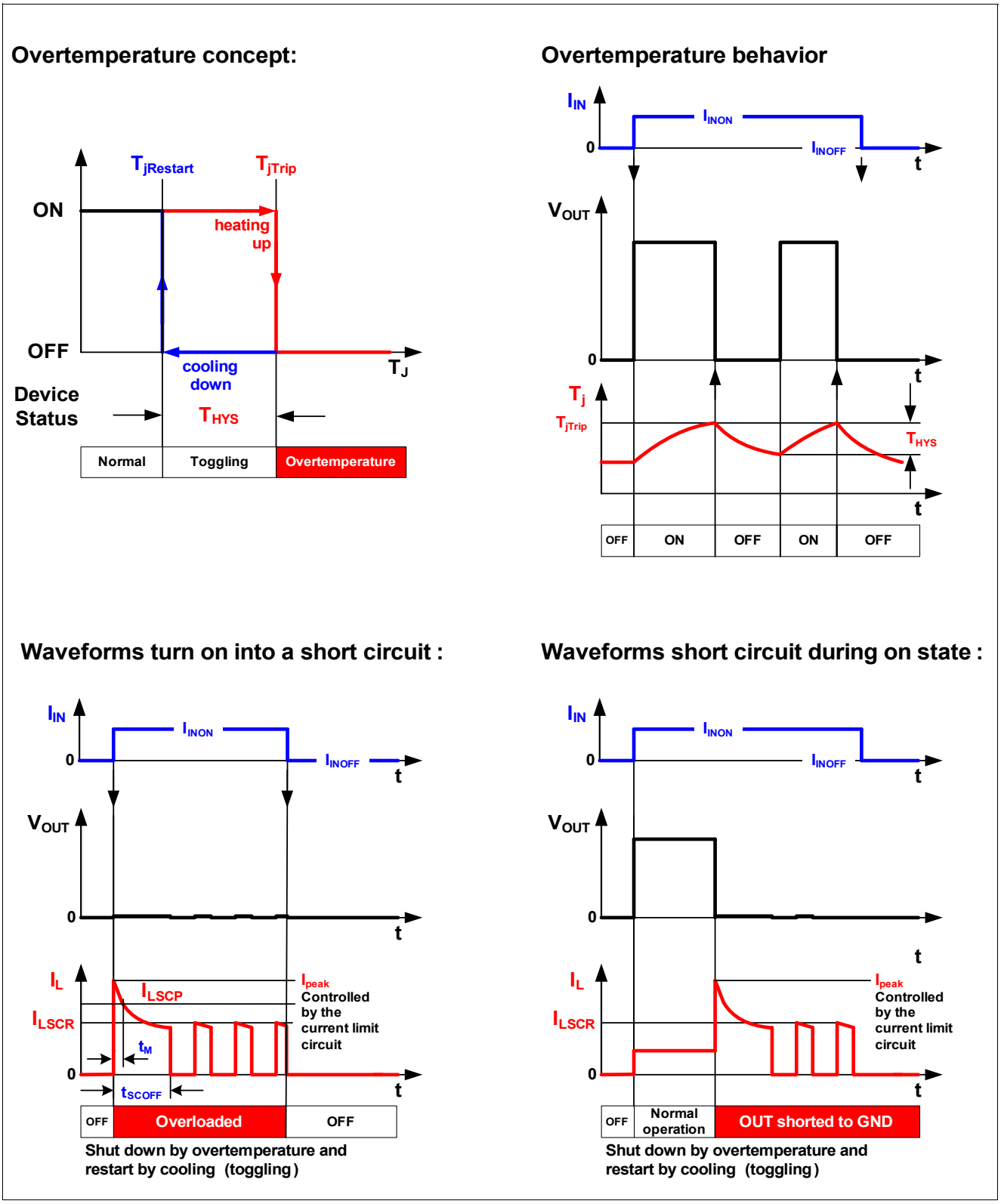
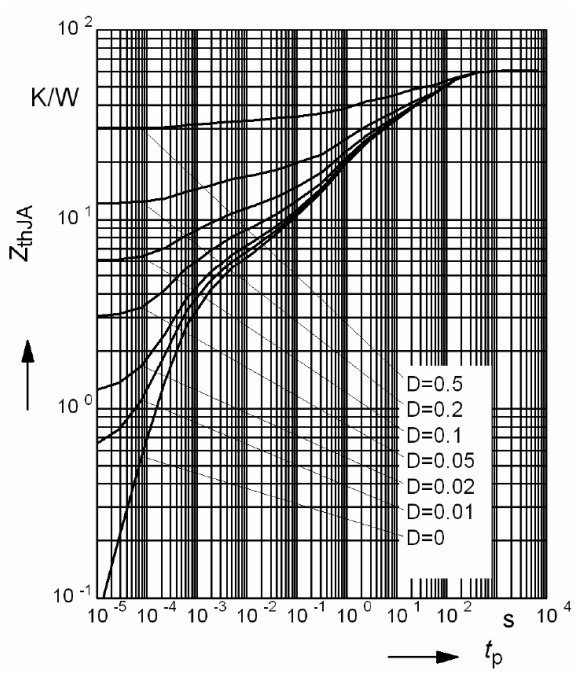


Figure 7 Protective behaviour waveforms of the ITS41k0S-ME-N

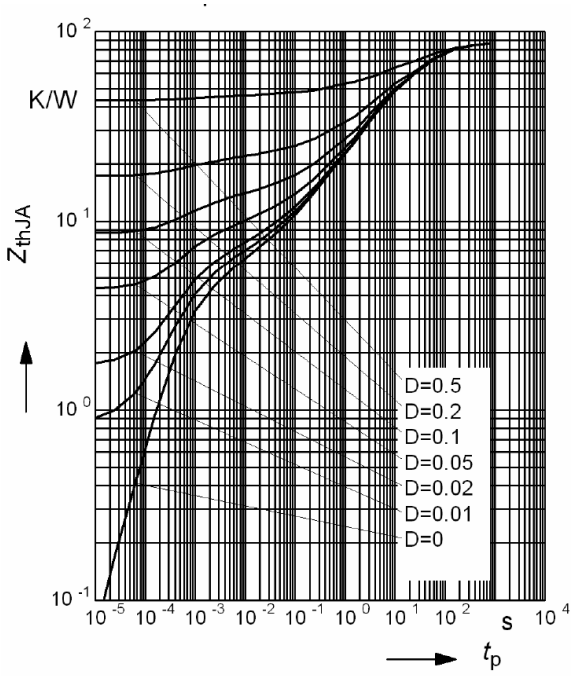
7 Typical Performance Graphs

Typical Performance Characteristics

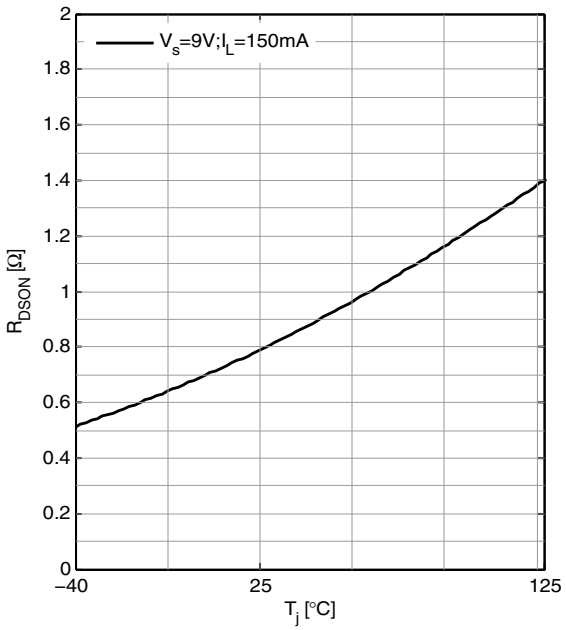
Transient Thermal Impedance Z_{thJA} versus Pulse Time t_p @ 6cm² heatsink area (D= t_p/T)



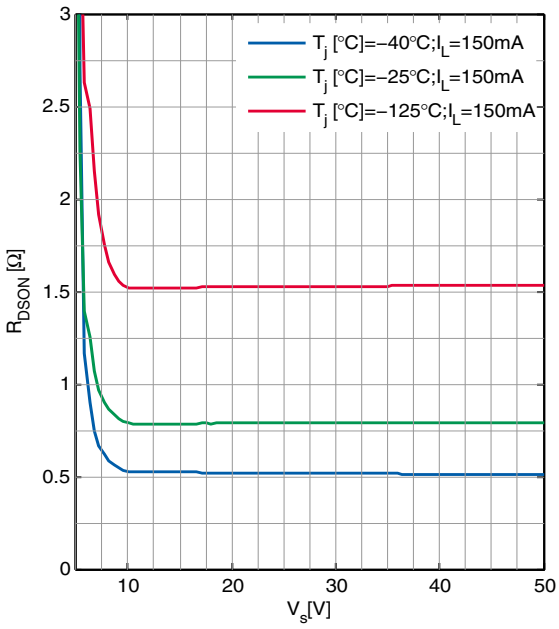
Transient Thermal Impedance Z_{thJA} versus Pulse Time t_p @ min. footprint (D= t_p/T)



On-Resistance R_{DSON} versus Junction Temperature T_J @ = V_S = 9V; I_L =150mA

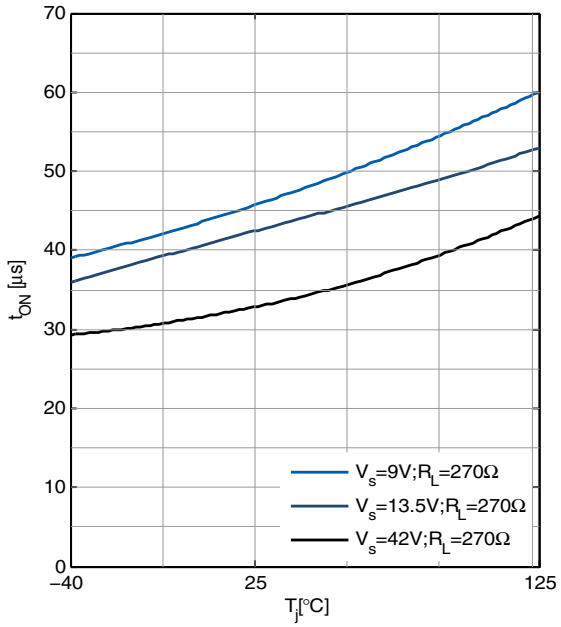


On-Resistance R_{DSON} versus Supply Voltage V_S = V_{bb} @ = I_L =150mA T_j =par.

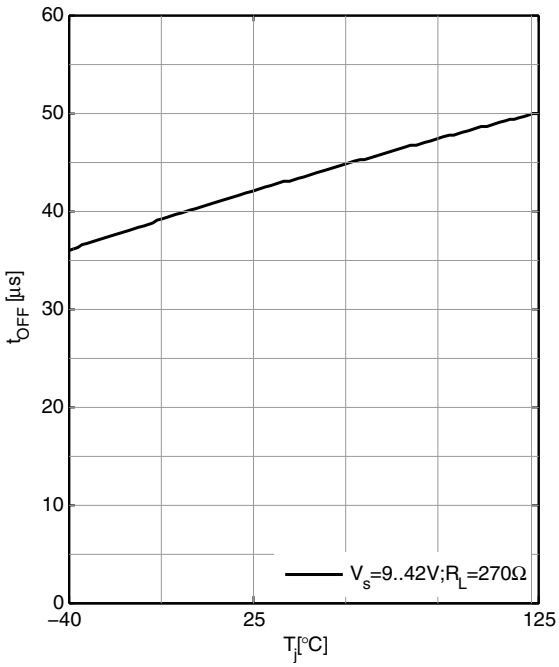


Typical Performance Characteristics

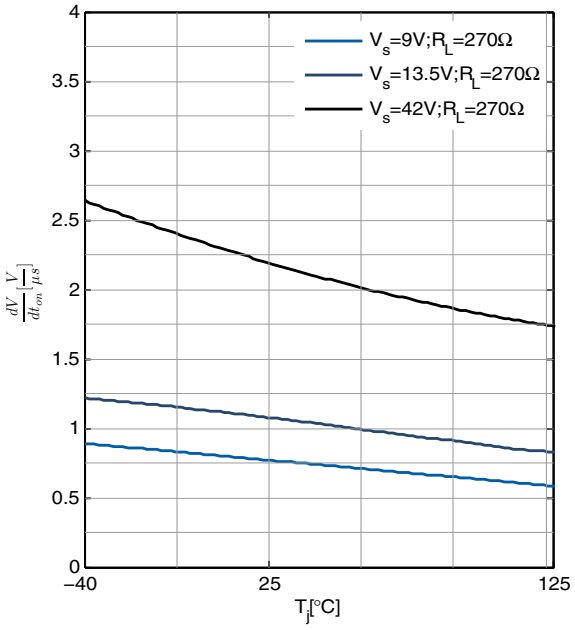
Switch ON Time t_{ON} versus Junction Temperature T_J @ = R_L = 270 Ω; V_S =par.



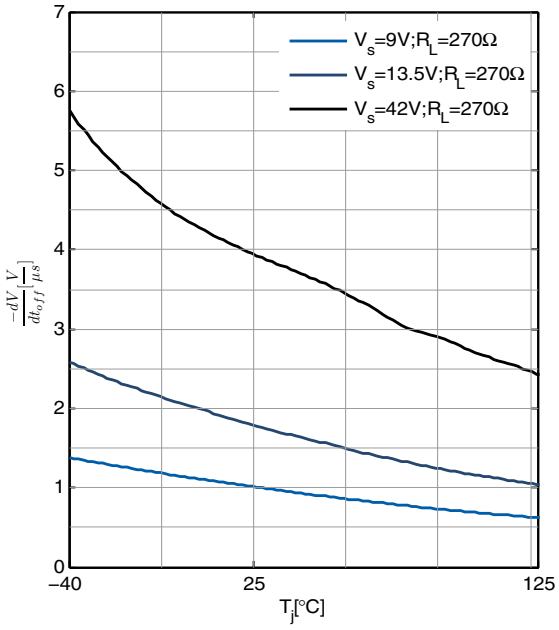
Switch OFF Time t_{OFF} versus Junction Temperature T_J @ = R_L = 270 Ω; V_S =par.



ON Slewrate SR_{ON} versus Junction Temperature T_J @ = R_L = 270 Ω; V_S =par.

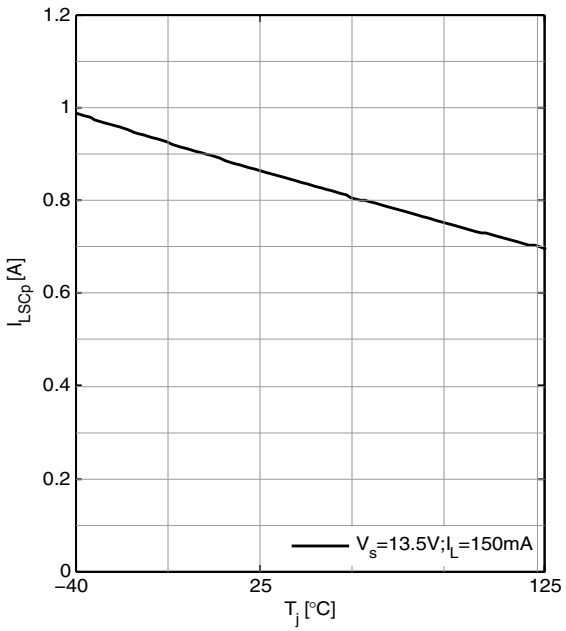


OFF Slewrate SR_{OFF} versus Junction Temperature T_J @ = R_L = 270 Ω; V_S =par.

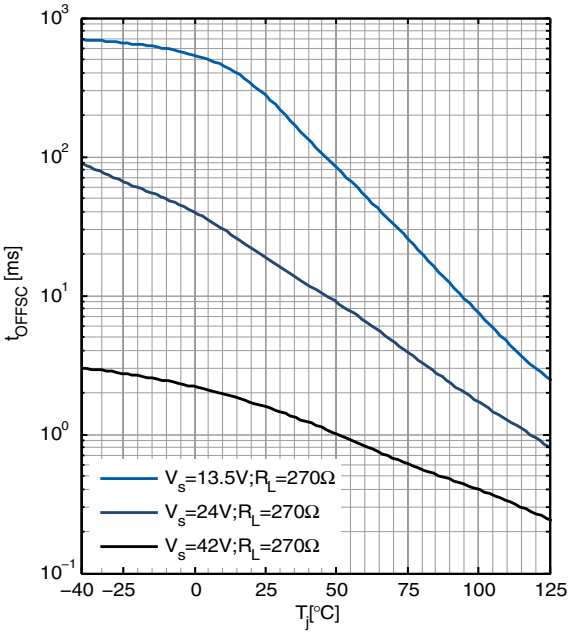


Typical Performance Characteristics

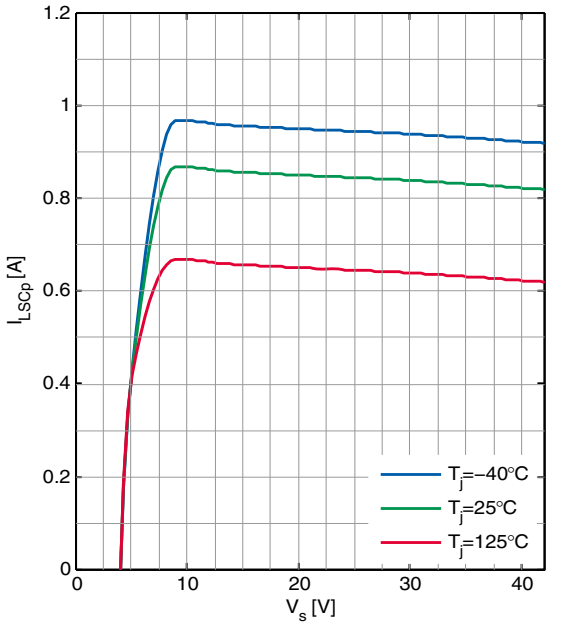
Initial Peak Short Circuit Current Limit I_{LSCP} versus Junction Temperature T_J @ V_S=13.5V; t_m =100µs



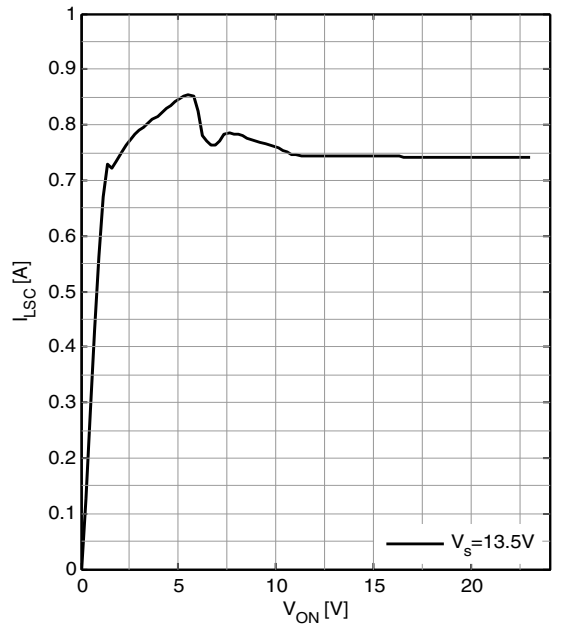
Initial Short Circuit Shutdown Time $t_{OFF\ SC}$ versus Junction Start-Temperature T_{JSTART} ; V_S=parameter



Initial Peak Short Circuit Current Limit I_{LSCP} versus Supply Voltage V_S = V_{bb} @ T_j =par.= 100µs.

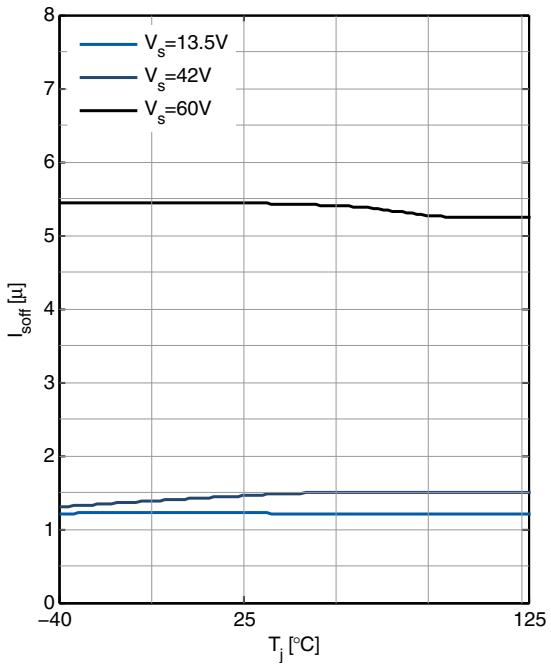


Current Limitation Characteristic I_{LSC} versus Drain Source Voltage Drop V_{DS} @ V_S =13.5 V



Typical Performance Characteristics

Stand By Current Consumption I_{SOFF} versus Junction Temperature T_J @ pin IN open



8 Package Outlines and Footprint

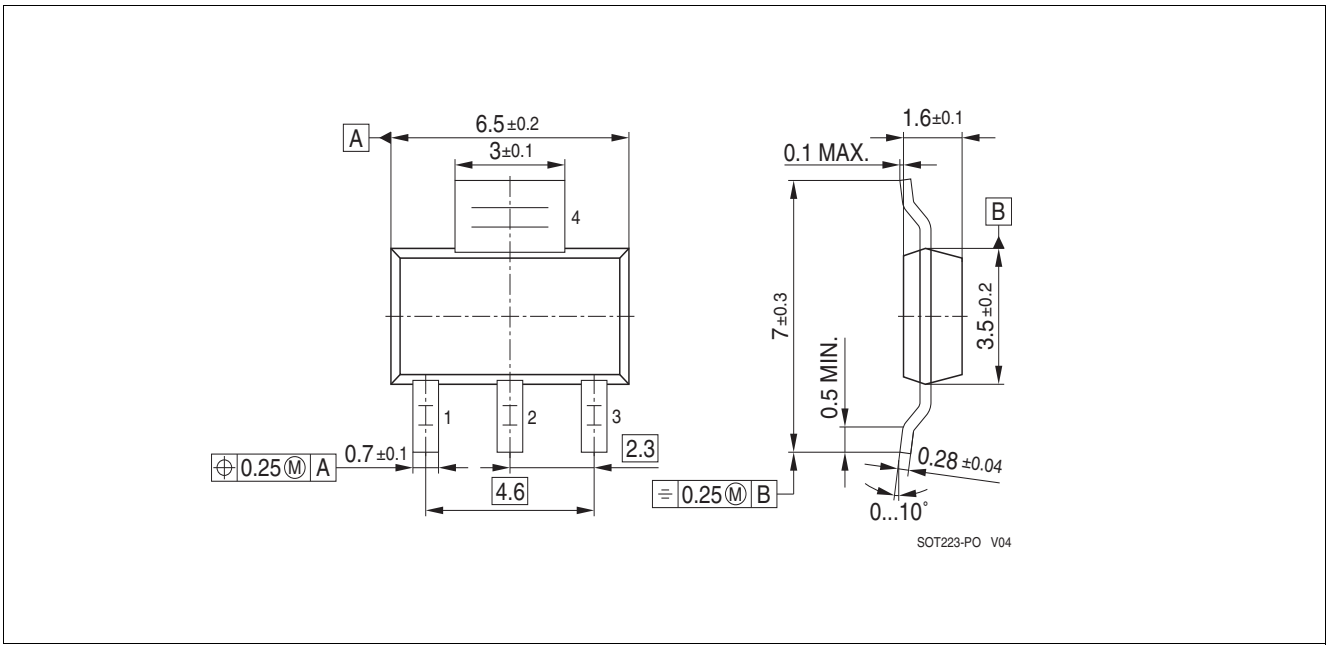


Figure 8 **PG-SOT223-4** (Plastic Dual Small Outline Package, RoHS-Compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020

9 Revision History

Revision	Date	Changes
1.0	2012-09-01	Datasheet release

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